XN01216 (XN1216)

Silicon NPN epitaxial planar type

For switching/digital circuits

Features

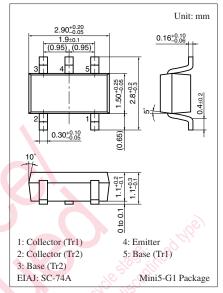
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR2216 (UN2216) × 2

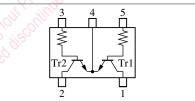
Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	50	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Collector current	I _C	100	mA	
Total power dissipation	P _T	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Marking Symbol: 9N

Internal Connection



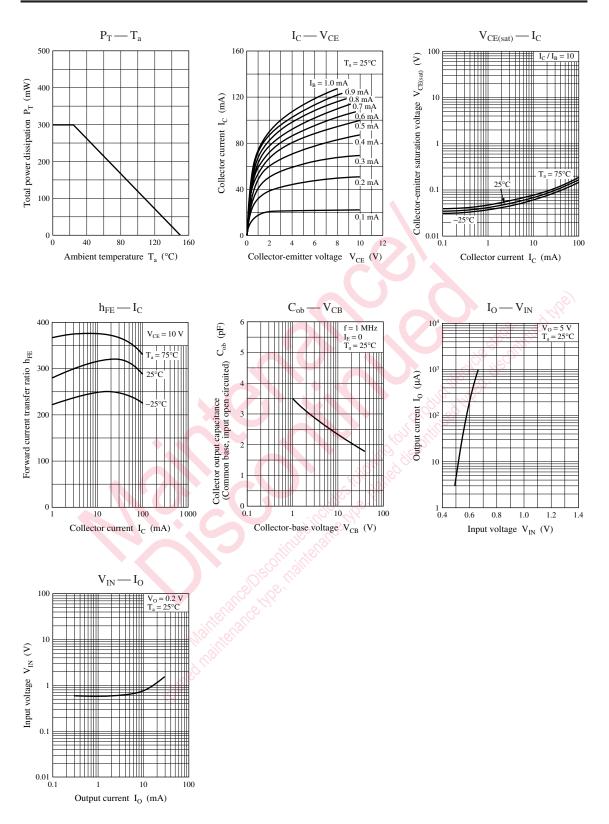
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 50 \text{ V}, \text{ I}_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 6 V, I_C = 0$			0.01	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	160		460	_
h _{FE} Ratio *	h _{FE(Small}	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	0.50	0.99		
Collector-emitter saturation voltage	/Large) V _{CE(sat)}	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	V _{OH}	$V_{CC} = 5 \text{ V}, \text{ V}_{B} = 0.5 \text{ MA}$ $V_{CC} = 5 \text{ V}, \text{ V}_{B} = 0.5 \text{ V}, \text{ R}_{I} = 1 \text{ k}\Omega$	4.9		0.25	V
Output voltage low-level	V _{OL}	$V_{CC} = 5 V, V_B = 0.5 V, R_L = 1 k\Omega$ $V_{CC} = 5 V, V_B = 2.5 V, R_L = 1 k\Omega$	4.7		0.2	V V
		$v_{\rm CC} = 5 v, v_{\rm B} = 2.5 v, \kappa_{\rm L} = 1 \text{K} \text{Z}$	200	47		
Input resistance	R ₁		-30%	4.7	+30%	kΩ
Transition frequency	f _T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.

Panasonic



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